

PECULIARITIES OF PIEZORESISTANCE
OF γ -IRRADIATED n -Si CRYSTALS
IN THE CASE OF SYMMETRIC POSITION
OF THE DEFORMATION AXIS RELATIVE
TO ALL ISOENERGETIC ELLIPSOIDS

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S u m m a r y

The piezoresistance of γ -irradiated n -Si crystals is studied in the case where $X \parallel J \parallel [111]$. A change of the energy gap between the deep energy level $E_C - 0.17$ eV and the conduction band valleys in n -Si arising due to a uniaxial deformation along the crystallographic direction $[111]$ is determined. It is shown that, for this crystallographic direction, the baric coefficient of a change of the energy gap is insignificant, since the shifts of the deepest level $E_C - 0.17$ eV and the conduction band valleys in n -Si under deformation are practically identical.